

**OptiMOS®3 Power-Transistor**
**Features**

- Fast switching MOSFET for SMPS
- Optimized technology for DC/DC converters
- Qualified according to JEDEC<sup>1)</sup> for target applications
- N-channel
- Normal level
- Excellent gate charge  $\times R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- Superior thermal resistance
- 100% Avalanche tested
- Pb-free plating; RoHS compliant

**Product Summary**

$V_{DS}$	40	V
$R_{DS(on),max}$	4.2	m $\Omega$
$I_D$	40	A

**PG-TSDSON-8**


Type	Package	Marking
BSZ042N04NS G	PG-TSDSON-8	042N04N


**Maximum ratings, at  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$V_{GS}=10\text{ V}, T_C=25\text{ }^\circ\text{C}$	40	A
		$V_{GS}=10\text{ V}, T_C=100\text{ }^\circ\text{C}$	40	
		$V_{GS}=10\text{ V}, T_A=25\text{ }^\circ\text{C}, R_{thJA}=60\text{ K/W}^2)$	18	
Pulsed drain current <sup>3)</sup>	$I_{D,pulse}$	$T_C=25\text{ }^\circ\text{C}$	160	
Avalanche current, single pulse <sup>4)</sup>	$I_{AS}$	$T_C=25\text{ }^\circ\text{C}$	20	
Avalanche energy, single pulse	$E_{AS}$	$I_D=20\text{ A}, R_{GS}=25\text{ }\Omega$	130	mJ
Gate source voltage	$V_{GS}$		$\pm 20$	V

<sup>1)</sup> J-STD20 and JESD22

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Power dissipation	$P_{\text{tot}}$	$T_C=25\text{ °C}$	69	W
		$T_A=25\text{ °C}$ , $R_{\text{thJA}}=60\text{ K/W}^2)$	2.1	
Operating and storage temperature	$T_j, T_{\text{stg}}$		-55 ... 150	°C
IEC climatic category; DIN IEC 68-1			55/150/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics**

Thermal resistance, junction - case	$R_{\text{thJC}}$		-	-	1.8	K/W
Device on PCB	$R_{\text{thJA}}$	6 cm <sup>2</sup> cooling area <sup>2)</sup>	-	-	60	

**Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified**
**Static characteristics**

Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0\text{ V}, I_{\text{D}}=1\text{ mA}$	40	-	-	V
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=36\text{ }\mu\text{A}$	2	-	4	
Zero gate voltage drain current	$I_{\text{DSS}}$	$V_{\text{DS}}=40\text{ V}, V_{\text{GS}}=0\text{ V}, T_j=25\text{ °C}$	-	0.1	1	$\mu\text{A}$
		$V_{\text{DS}}=40\text{ V}, V_{\text{GS}}=0\text{ V}, T_j=125\text{ °C}$	-	10	100	
Gate-source leakage current	$I_{\text{GSS}}$	$V_{\text{GS}}=20\text{ V}, V_{\text{DS}}=0\text{ V}$	-	10	100	nA
Drain-source on-state resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}}=10\text{ V}, I_{\text{D}}=20\text{ A}$	-	3.5	4.2	m $\Omega$
Gate resistance	$R_{\text{G}}$		-	1.8	-	$\Omega$
Transconductance	$g_{\text{fs}}$	$ V_{\text{DS}} >2 I_{\text{D}} R_{\text{DS(on)max}}, I_{\text{D}}=20\text{ A}$	25	50	-	S

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

<sup>3)</sup> See figure 3 for more detailed information

<sup>4)</sup> See figure 13 for more detailed information

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=20\text{ V},$ $f=1\text{ MHz}$	-	2800	3700	pF
Output capacitance	$C_{oss}$		-	820	1100	
Reverse transfer capacitance	$C_{rss}$		-	30	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=20\text{ V}, V_{GS}=10\text{ V},$ $I_D=20\text{ A}, R_G=1.6\ \Omega$	-	14	-	ns
Rise time	$t_r$		-	3.4	-	
Turn-off delay time	$t_{d(off)}$		-	20	-	
Fall time	$t_f$		-	4.2	-	

**Gate Charge Characteristics<sup>5)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=20\text{ V}, I_D=20\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	14	-	nC
Gate charge at threshold	$Q_{g(th)}$		-	8.5	-	
Gate to drain charge	$Q_{gd}$		-	4.3	-	
Switching charge	$Q_{sw}$		-	10	-	
Gate charge total	$Q_g$		-	35	46	
Gate plateau voltage	$V_{plateau}$		-	5.0	-	
Gate charge total, sync. FET	$Q_{g(sync)}$	$V_{DS}=0.1\text{ V},$ $V_{GS}=0\text{ to }10\text{ V}$	-	33	-	nC
Output charge	$Q_{oss}$	$V_{DD}=20\text{ V}, V_{GS}=0\text{ V}$	-	30	-	

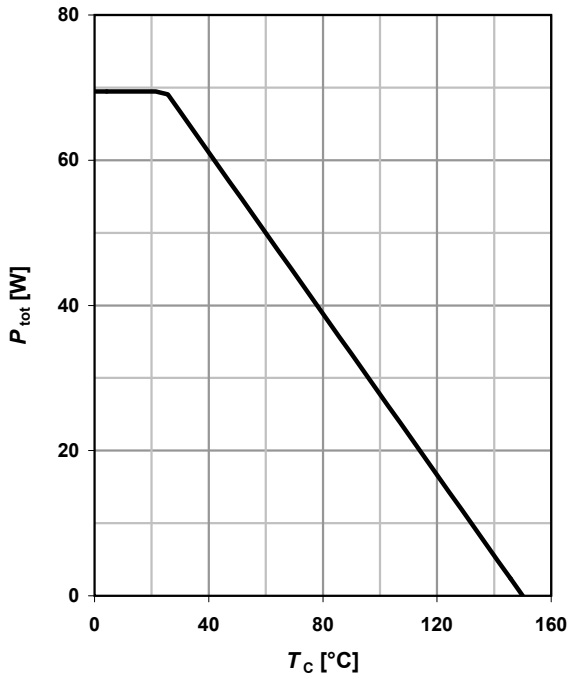
**Reverse Diode**

Diode continuous forward current	$I_S$	$T_C=25\text{ }^\circ\text{C}$	-	-	40	A
Diode pulse current	$I_{S,pulse}$		-	-	160	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=20\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	0.84	1.2	V
Reverse recovery charge	$Q_{rr}$	$V_R=20\text{ V}, I_F=I_S,$ $di_F/dt=400\text{ A}/\mu\text{s}$	-	28	-	nC

<sup>5)</sup> See figure 16 for gate charge parameter definition

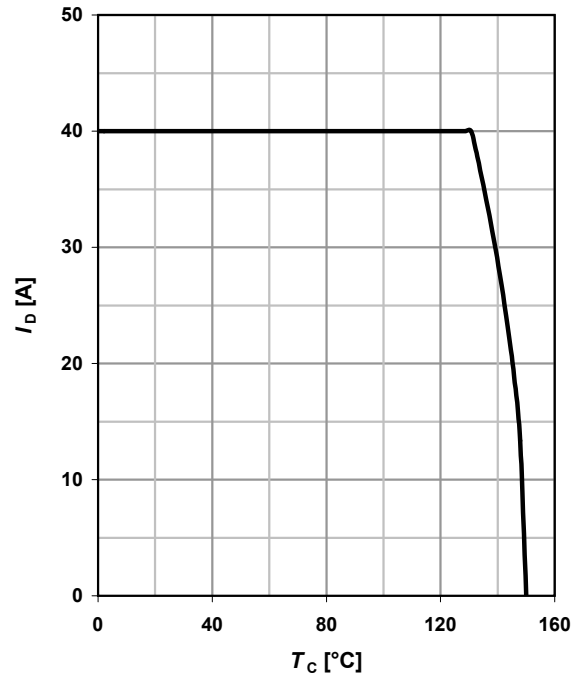
**1 Power dissipation**

$$P_{tot} = f(T_C)$$



**2 Drain current**

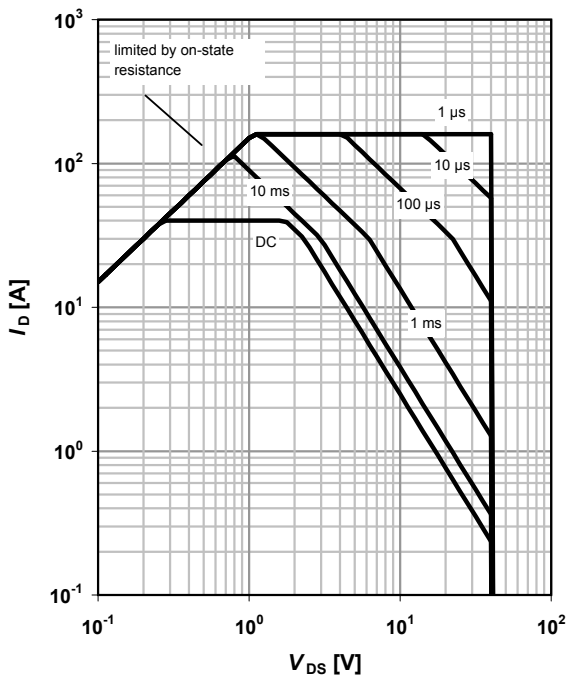
$$I_D = f(T_C); V_{GS} \geq 10 \text{ V}$$



**3 Safe operating area**

$$I_D = f(V_{DS}); T_C = 25 \text{ °C}; D = 0$$

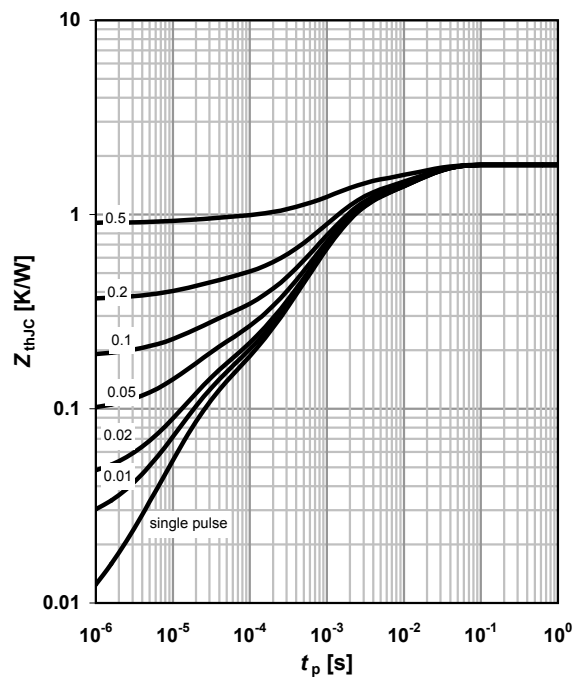
parameter:  $t_p$



**4 Max. transient thermal impedance**

$$Z_{thJC} = f(t_p)$$

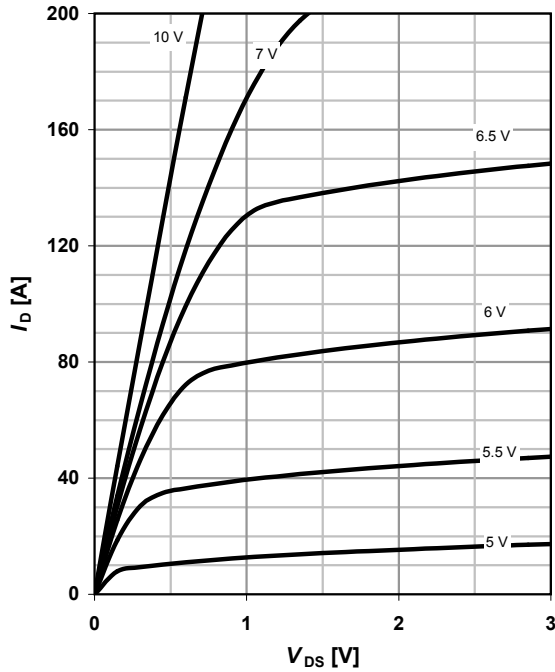
parameter:  $D = t_p / T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

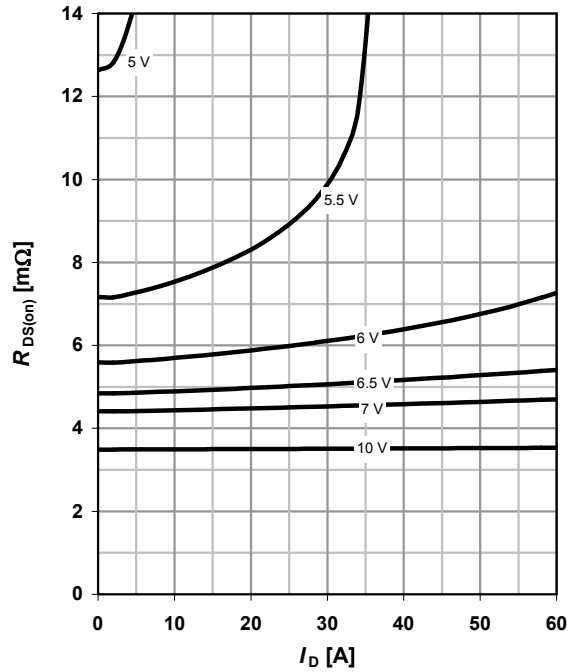
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

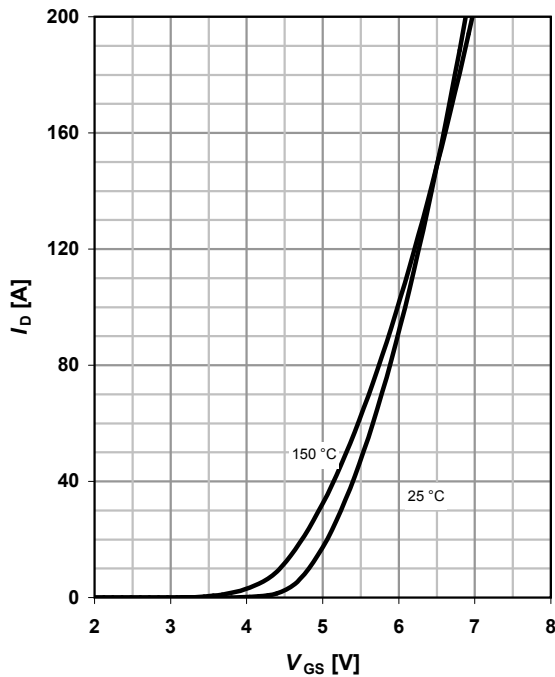
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

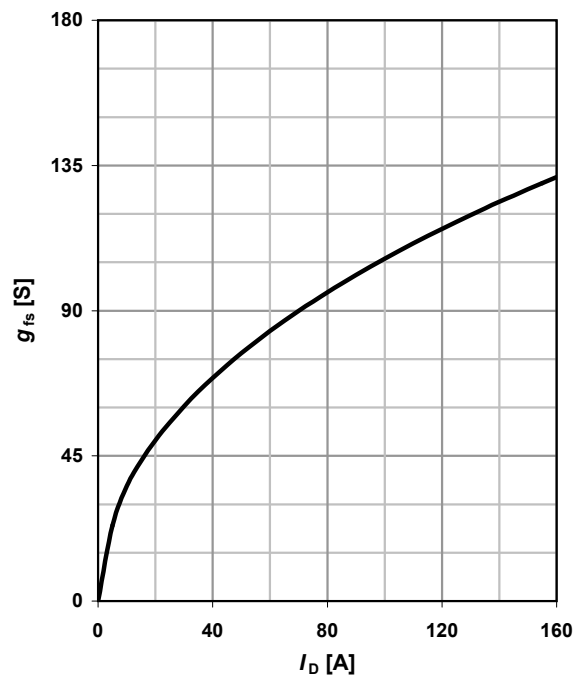
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



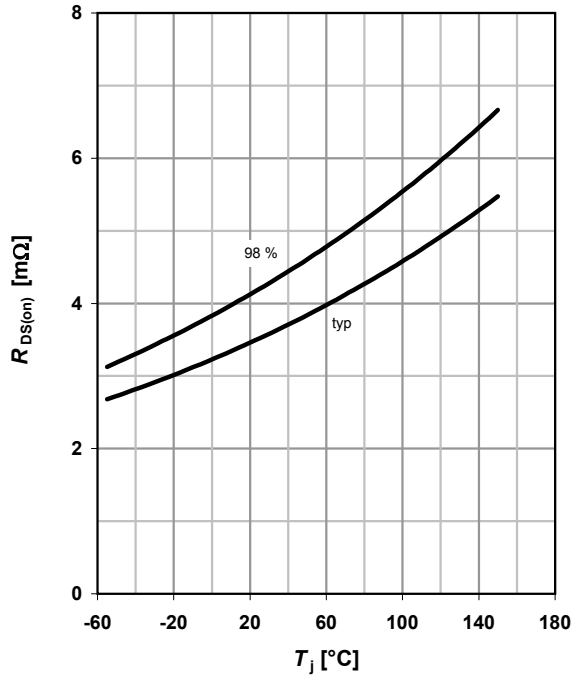
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$



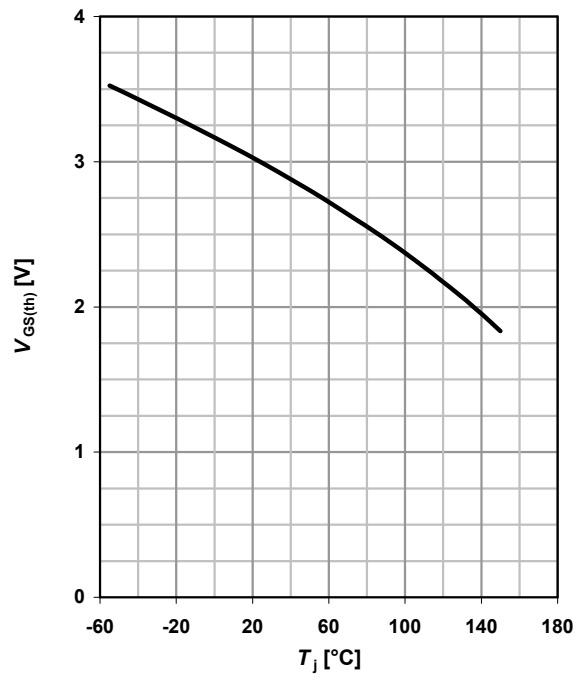
**9 Drain-source on-state resistance**

$R_{DS(on)} = f(T_j); I_D = 20 \text{ A}; V_{GS} = 10 \text{ V}$



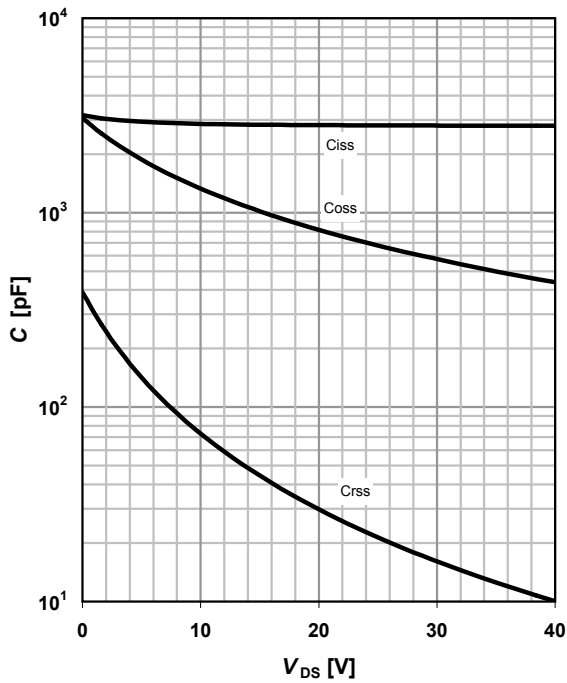
**10 Typ. gate threshold voltage**

$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = 36 \mu\text{A}$



**11 Typ. capacitances**

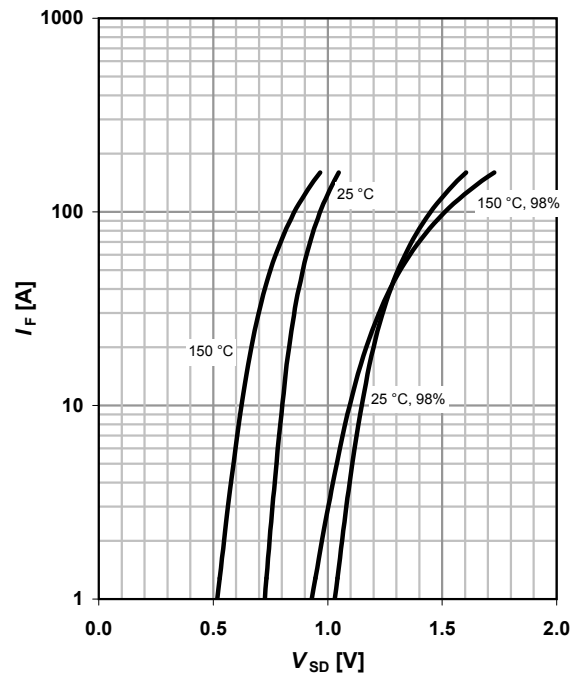
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F = f(V_{SD})$

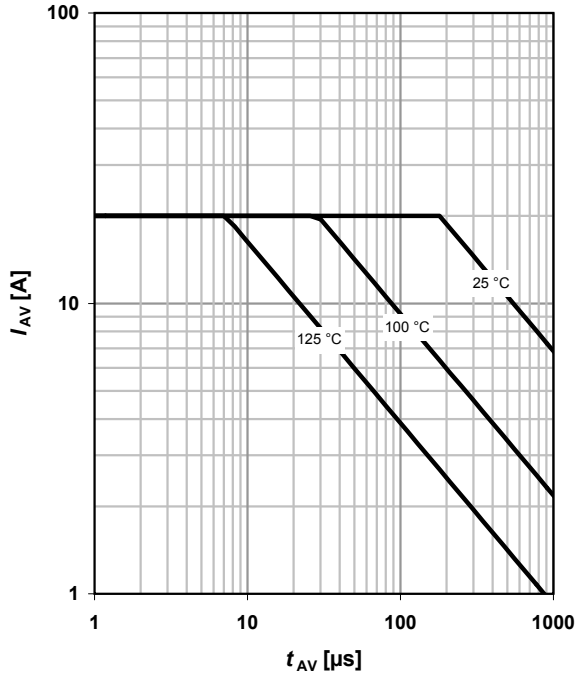
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

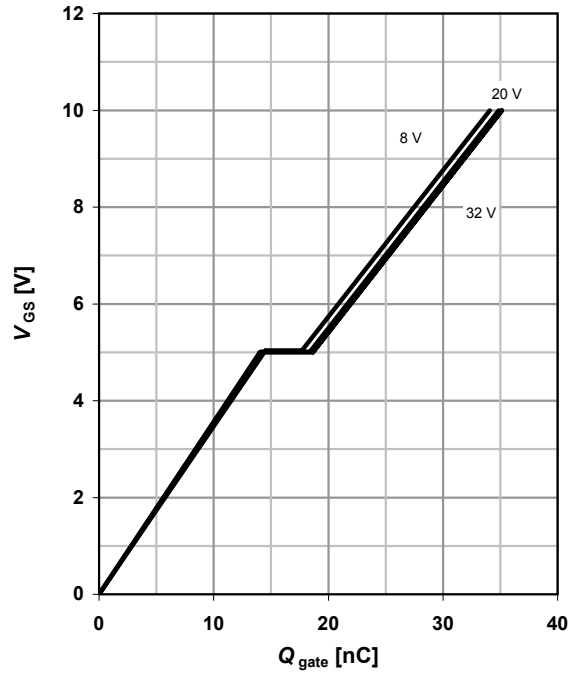
parameter:  $T_{j(start)}$



**14 Typ. gate charge**

$V_{GS}=f(Q_{gate}); I_D=20 \text{ A pulsed}$

parameter:  $V_{DD}$



**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

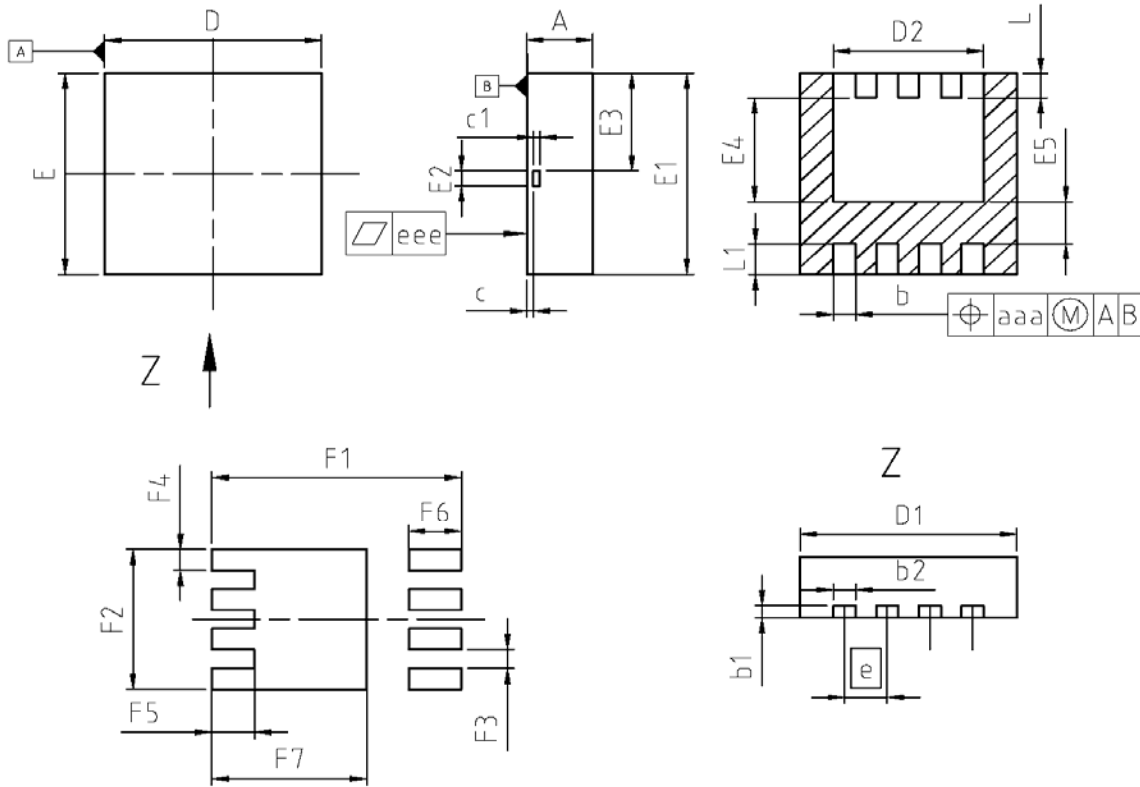


**16 Gate charge waveforms**



Package Outline

PG-TSDSON-8



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.95	1.00	0.037	0.039
b	0.25	0.35	0.010	0.014
b1	0.10	0.30	0.004	0.012
b2	0.20	0.40	0.008	0.016
c	0.00	0.20	0.000	0.008
D=D1	3.20	3.40	0.126	0.134
D2	2.15	2.35	0.085	0.093
E=E1	3.20	3.40	0.126	0.134
E2	0.10	0.30	0.004	0.012
E3	1.35	1.55	0.053	0.061
E4	1.60	1.80	0.063	0.071
E5	0.66	0.86	0.026	0.034
e	0.60	0.70	0.024	0.028
N	8		8	
L	0.31	0.51	0.012	0.020
L1	0.33	0.53	0.013	0.021
aaa	0.25		0.010	
eee	0.05		0.002	
F1	3.70	3.90	0.146	0.154
F2	2.19	2.39	0.086	0.094
F3	0.21	0.41	0.008	0.016
F4	0.24	0.44	0.009	0.017
F5	0.55	0.75	0.022	0.030
F6	0.70	0.90	0.028	0.035
F7	2.28	2.46	0.089	0.097

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